

/ Descriptions

TO-220F M M E N 3 MOS 6 0 Z 1 N-CHANNEL MOSFET in a TO-220F Plastic Package.

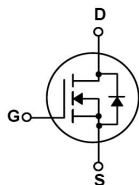
/ Features

$H_{fs} \geq U_{GS} \geq U_{th}$ / $\Delta H_{fs} \geq 10$
Low gate charge, low c_{rss} , fast switching.

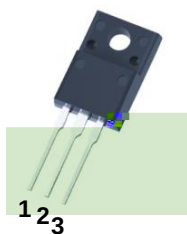
/ Applications

$f_{sw} \leq 100$ kHz / GF2GF ≥ 10 A / $\Delta H_{fs} \geq 10$
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN 1 χ G

PIN 2 χ D

PIN 3 χ S

/ h_{FE} Classifications & Marking

$\delta M 1 \cup "$ See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	5.0	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	2.6	A
Drain Current - Pulsed	I_{DM}	18	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	210	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.5	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	54	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	
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/ Package Dimensions



